6.730 Physics for Solid State Applications

Lecture 20: Impurity States

<u>Outline</u>

- Semiclassical Equations of Motion
- Review of Last Time: Effective Mass Hamiltonian
- Example: Impurity States

k.p Hamiltonian

$$H_{k+q} = H_k + \frac{\hbar^2}{m}q \cdot \left(\frac{1}{i}\nabla + k\right) + \frac{\hbar^2}{2m}q^2$$

Taylor Series expansion of energies...

$$E_n(k+q) = E_n(k) + \sum_i \frac{\partial E_n}{\partial k_i} q_i + \frac{1}{2} \sum_{ij} \frac{\partial^2 E_n}{\partial k_i \partial k_j} q_i q_j + O(q^3)$$

Matching terms to first order in q...

$$\frac{\partial E_n}{\partial k_i} = \int dr \, \tilde{u}_{nk}^* \frac{\hbar^2}{m} \left(\frac{1}{i}\nabla + k\right)_i \, \tilde{u}_{nk}$$
$$\frac{\partial E_n}{\partial k_i} = \int dr \, \psi_{nk}^* \frac{\hbar}{m} \hat{p}_i \, \psi_{nk} = \frac{\hbar}{m} < \hat{p}_i >$$

$$<\mathbf{v}_n(\mathbf{k})>=rac{<\mathbf{p}>}{\mathbf{m}}=rac{1}{\hbar}
abla_\mathbf{k}\mathbf{E}_n(\mathbf{k})$$

Semiclassical Equation of Motion

$$\frac{d \langle \hat{T}_R \rangle}{dt} = \frac{i}{\hbar} \langle [\hat{V}_{ext}, \hat{T}_R] \rangle = eE \frac{i}{\hbar} \langle [\hat{r}, \hat{T}_R] \rangle$$

Plugging in this commutation relation into the equation of motion...

$$\frac{d < \hat{T}_R >}{dt} = eE\frac{i}{\hbar} \langle [\hat{r}, \hat{T}_R] \rangle$$
$$= eER \frac{i}{\hbar} \langle \hat{T}_R \rangle$$

Solving the simple differential equation...

$$\langle \hat{T}_R \rangle = e^{i e E R t / \hbar}$$

From Bloch's Thm. We know the eigenvalues of T_{R} ...

$$T_R \psi(r) = e^{ikR} \psi(r) \qquad \langle \hat{T}_R \rangle = e^{ikR}$$

 $k = \frac{eE}{\hbar}t + k_0$ $eE = \hbar \frac{dk}{dt}$ $\mathbf{F}_{\text{ext}} = \hbar \frac{d\mathbf{k}}{dt}$

Electron Motion in a Uniform Electric Field 2-D Crystal



http://www.physics.cornell.edu/sss/ziman/ziman.html

Properties of the Translation Operator

Definition of the translation operator...

$$\widehat{T}_{\mathbf{R}}\psi(\mathbf{r}) = \psi(\mathbf{r} + \mathbf{R})$$

Bloch functions are eigenfunctions of the lattice translation operator...

$$\widehat{T}_{\mathbf{R}}\psi(\mathbf{r}) = \mathbf{c}(\mathbf{R})\psi(\mathbf{r})$$

$$c(\mathbf{R}) = e^{\mathbf{i}\mathbf{k}\cdot\mathbf{R}}$$

Lattice translation operator commutes with the lattice Hamiltonian ($V_{ext}=0$)

$$[\hat{T}_{\mathbf{R}}, H(\mathbf{r})] = \mathbf{0}$$

The translation operator commutes with other translation operators...

$$[\hat{T}_{\mathbf{R}_1}, \hat{T}_{\mathbf{R}_2}] = 0$$

Properties of the Translation Operator

Lets see what the action of the following operator is...

$$\left[e^{-R\frac{\partial}{\partial x}}\right]f(x) = \left(1 - R\frac{\partial}{\partial x} + \frac{1}{2!}R^2\frac{\partial^2}{\partial x^2} - \frac{1}{3!}R^3\frac{\partial^3}{\partial x^3} + \cdots\right)f(x)$$

$$= f(x) - Rf'(x) + \frac{1}{2!}R^2f''(x) - \frac{1}{3!}R^3f'''(x) + \cdots$$

$$= f(x - R)$$

This is just the translation operator...

$$e^{-\mathbf{R}\cdot\nabla_{\mathbf{r}}}f(\mathbf{r}) = f(\mathbf{r} - \mathbf{R})$$

 $T_{-\mathbf{R}}f(\mathbf{r}) = e^{-\mathbf{R}\cdot\nabla_{\mathbf{r}}}f(\mathbf{r})$

Another Look at Electronic Bandstructure



As we will see, it is often convenient to represent the bandstructure by its inverse Fourier series expansion...

$$E_n(k) = \sum_{\ell} E_n(R_{\ell}) e^{ik \cdot R_{\ell}}$$

Wavefunction of Electronic Wavepacket

The eigenfunction for $k \sim k_0$ are approximately...

$$\psi_{n,k}(r) = e^{ik \cdot r} u_{n,k}(r) \approx e^{i(k-k_0) \cdot r} \psi_{n,k_0}(r)$$

A wavepacket can therefore be constructed from Bloch states as follows...

$$\psi'_{n}(r,t) = \sum_{k} c_{n}(k,t)\psi_{n,k}(r)$$

$$\psi'_{n}(r,t) = \underbrace{G_{n}(r,t)}_{\text{envelope function}} \underbrace{u_{n,k_{0}}(r)}_{\text{Bloch amplitude}}$$

Since we construct wavepacket from a small set of k's...

$$\Delta k \ll rac{2\pi}{a}$$
 and $\Delta r \gg a$

...the envelope function must vary slowly...wavepacket must be large...

 $\Delta r \gg a$

Summary of Last Time

Without explicitly knowing the Bloch functions, we can solve for the envelope functions...

$$\left(\hat{H}_0 + \hat{V}_{ext}(r)\right) G_n(r,t) = i\hbar \frac{\partial G_n(r,t)}{\partial t}$$

Bandstructure shows up in here... $\hat{H}_0 = \sum_{\ell} E_n(R_{\ell}) \hat{T}_{R_{\ell}}$

The envelope functions are sufficient to determine the expectation of position and crystal momentum for the system...

$$< r(t) >_G = rac{< G_n(r,t) |r| G_n(r,t) >}{< G_n(r,t) |G_n(r,t) >} = < r(t) >$$

$$\langle p \rangle_G = \frac{\langle G_n(r,t) | \hat{p} | G_{(r,t)} \rangle}{\langle G_n(r,t) | G_n(r,t) \rangle} \approx \hbar k_0$$

Using Bandstructure in Effective Mass Hamiltonian

$$\left(\hat{H}_0 + \hat{V}_{ext}(r)\right) G_n(r,t) = i\hbar \frac{\partial G_n(r,t)}{\partial t}$$

where
$$\hat{H}_0 = \sum_{\ell} E_n(R_{\ell}) \hat{T}_{R_{\ell}}$$

Bandstructure shows up in here...

$$E_n(k) = \sum_{\ell} E_n(R_{\ell}) e^{ik \cdot R_{\ell}}$$

$$\hat{H}_{0} = \sum_{\ell} E_{n}(R_{\ell}) \, \hat{T}_{R_{\ell}}$$
$$= \sum_{\ell} E_{n}(R_{\ell}) \, e^{R_{\ell} \cdot \nabla_{r}}$$

For example...

$$E_N(k) = \left(\frac{\hbar^2}{2m^*}\right)k^2$$

$$\hat{H}_0 = -\left(\frac{\hbar^2}{2m^*}\right)\nabla_r^2$$

Replace silicon (IV) with group V atom...

$$V(\mathbf{r}) = \sum_{\mathbf{R}_{\ell}} \underbrace{V_{\text{Si}}(\mathbf{r} - \mathbf{R}_{\ell})}_{\text{periodic}} + \underbrace{\left[V_{\text{AS}}(\mathbf{r}) - V_{\text{Si}}(\mathbf{r})\right]}_{\Phi_{\text{ext}}(\mathbf{r})}$$
$$\Phi_{\text{ext}}(\mathbf{r}) = -\frac{e^2}{4\pi\epsilon_{\text{Si}}} \frac{1}{|\mathbf{r}|}$$

$$E_N(k) = E_c + \frac{\hbar^2 k^2}{2m^*} + \dots$$

$$\left(-\frac{\hbar^2 \nabla^2}{2m^*} + E_c - \frac{e^2}{4\pi\epsilon |\mathbf{r}|}\right) G_N(r,t) = -\frac{\hbar}{i} \frac{\partial G_N(r,t)}{\partial t}$$
$$G_N(r,t) = G_N(r)e^{-iE_d t/\hbar}$$

This is a central potential problem, like the hydrogen atom...

$$\left(-\frac{\hbar^2 \nabla^2}{2m^*} - \frac{e^2}{4\pi\epsilon |r|}\right) G_N(r) = (E_d - E_c)G_N(r)$$

$$E_{l} = E_{d} - E_{c} = -\frac{m^{*}e}{2(4\pi\epsilon)^{2}\hbar^{2}l^{2}} = -\frac{13.6}{l^{2}} \left(\frac{m^{*}\epsilon_{0}^{2}}{m\epsilon^{2}}\right) \text{ eV}$$

with $l = 1, 2, 3, 4, \dots$

Hydrogenic wavefunction with an equivalent Bohr radius..

$$G_1(r) = Ae^{-r/r_0}$$
 where $r_0 = \frac{\epsilon \hbar^2}{m^* e^2} = \epsilon \frac{m}{m^*} (0.53 \text{ A})$

Donor ionization energy...

$$E_d = E_c - \frac{13.56}{l^2 \epsilon^2} \frac{m^*}{m} \text{ eV}$$



$$g(E) = g_{\mathsf{Si}}(E) + \sum_{l} g_{l}\delta(E - E_{l})$$

When there are N_d donor impurities...

$$g(E) = g_{\mathsf{Si}}(E) + N_d \sum_{l} g_l \delta(E - E_l)$$



Replace silicon (IV) with group III atom...

$$V(\mathbf{r}) = \sum_{\mathbf{R}_{\ell}} \underbrace{V_{\text{Si}}(\mathbf{r} - \mathbf{R}_{\ell})}_{\text{periodic}} + \underbrace{\left[V_{\text{B}}(\mathbf{r}) - V_{\text{Si}}(\mathbf{r})\right]}_{\Phi_{\text{ext}}(\mathbf{r})}$$
$$\Phi_{\text{ext}}(r) = \frac{e^2}{4\pi\epsilon} \frac{1}{|r|}$$

$$E(k) = E_v - \frac{\hbar^2 k^2}{2m^*} + \dots$$

$$\left(E_v + \frac{\hbar^2 \nabla^2}{2m^*} + \frac{e^2}{4\pi\epsilon |r|}\right) G_N(r,t) = -\frac{\hbar}{i} \frac{\partial G_N(r,t)}{\partial t}$$

$$G_N(r,t) = G_N(r)e^{-iE_at/\hbar}$$

Another central potential problem...

$$\left(-\frac{\hbar^2 \nabla^2}{2m^*} - \frac{e^2}{4\pi\epsilon |r|}\right) G_N(r) = (E_v - E_a)G_N(r)$$

$$E_{l} = E_{v} - E_{a} = -\frac{m^{*}e}{2(4\pi\epsilon)^{2}\hbar^{2}l^{2}} = -\frac{13.6}{l^{2}} \left(\frac{m^{*}\epsilon_{0}^{2}}{m\epsilon^{2}}\right) \text{ eV}$$

with $l = 1, 2, 3, 4, \dots$

Hydrogenic wavefunction with an equivalent Bohr radius..

$$G_1(r) = Ae^{-r/r_0}$$
 where $r_0 = \frac{\epsilon \hbar^2}{m^* e^2} = \epsilon \frac{m}{m^*} (0.53 \text{ \AA})$

Acceptor ionization energy...

 $E_a = E_v + \frac{13.56}{l^2 \epsilon^2} \frac{m^*}{m} \text{ eV}$